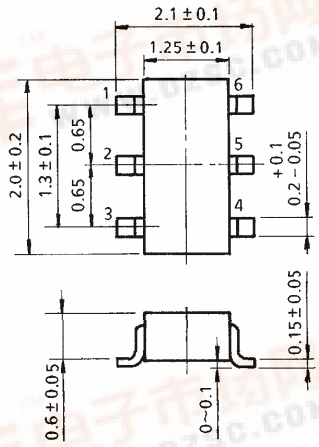
TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL PLANAR TYPE

MT6P06T

VHF~UHF BAND LOW NOISE AMPLIFIER APPLICATIONS

Unit in mm

- TWO devices are built in to the super-thin and ultra super mini (6 pins) package : TU6



1. EMITTER 1
2. EMITTER 2
3. BASE 2
4. COLLECTOR 2
5. BASE 1
6. COLLECTOR 1

JEDEC	—
EIAJ	—
TOSHIBA	2-2JA1A

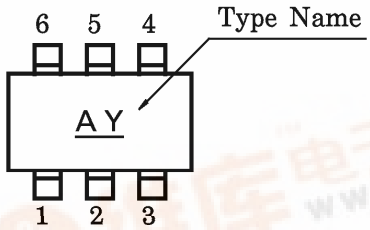
MOUNTED DEVICES

	Q1 / Q2 : SSM (TESM)
Three-pins (SSM / TESM) mold products are corresponded.	MT3S06S (MT3S06T)

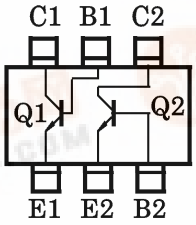
MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	Q1 / Q2	UNIT
Collector-Base Voltage	V_{CBO}	10	V
Collector-Emitter Voltage	V_{CEO}	5	V
Emitter-Base Voltage	V_{EBO}	1.5	V
Collector Current	I_C	15	mA
Base Current	I_B	7	mA
Collector Power Dissipation	P_C	120	mW
Junction Temperature	T_j	125	°C
Storage Temperature Range	T_{stg}	−55~125	°C

MARKING



PIN ASSIGNMENT (TOP VIEW)



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ELECTRICAL CHARACTERISTICS Q1 / Q2 (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	V_{CB} = 5 V, I_E = 0	—	—	0.1	μA
Emitter Cut-off Current	I_{EBO}	V_{EB} = 1 V, I_C = 0	—	—	1	μA
DC Current Gain	h_{FE}	V_{CE} = 1 V, I_C = 5 mA	70	—	140	—
Transition Frequency	f_T	V_{CE} = 3 V, I_C = 5 mA	7	10	—	GHz
Insertion Gain	$\|S_{21e}\|^2$ (1)	V_{CE} = 1 V, I_C = 5 mA, f = 2 GHz	—	7.5	—	dB
	$\|S_{21e}\|^2$ (2)	V_{CE} = 3 V, I_C = 7 mA, f = 2 GHz	4.5	8	—	dB
Noise Figure	NF (1)	V_{CE} = 1 V, I_C = 3 mA, f = 2 GHz	—	1.7	3	dB
	NF (2)	V_{CE} = 3 V, I_C = 3 mA, f = 2 GHz	—	1.6	3	dB
Reverse Transfer Capacitance	C_{re}	V_{CB} = 1 V, I_E = 0, f = 1 MHz (Note)	—	0.35	0.75	pF

(Note) : C_{re} is measured by 3 terminal method with capacitance bridge.

HANDLING PRECAUTION

When handling individual devices (which are not yet mounting on a circuit board), be sure that the environment is protected against electrostatic electricity. Operators should wear anti-static clothing, and containers and other objects that come into direct contact with devices should be made of anti-static materials.